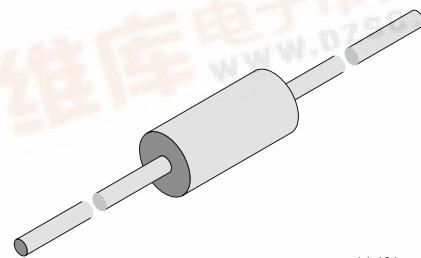




2.0A Glass Passivated Rectifier

Features

- Glass passivated die construction
- Diffused junction
- High current capability and low forward voltage drop
- Surge overload rating to 65A peak
- Plastic material – UL Recognition flammability classification 94V-0



14 421

Absolute Maximum Ratings

 $T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage =Working peak reverse voltage =DC Blocking voltage		LT2A01G	V_{RRM} = V_{RWM} = V_R	50	V
		LT2A02G		100	V
		LT2A03G		200	V
		LT2A04G		400	V
		LT2A05G		600	V
		LT2A06G		800	V
		LT2A07G		1000	V
Peak forward surge current			I_{FSM}	65	A
Average forward current	$T_A=55^\circ\text{C}$		I_{FAV}	2	A
Junction and storage temperature range			$T_j=T_{stg}$	-65...+175	°C

Electrical Characteristics

 $T_j = 25^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=2\text{A}$		V_F			1.1	V
Reverse current	$T_A=25^\circ\text{C}$		I_R			5	μA
	$T_A=100^\circ\text{C}$		I_R			200	μA
I^2t Rating for fusing			I^2t			17.5	A^2s
Diode capacitance	$V_R=4\text{V}$, $f=1\text{MHz}$		C_D	40			pF
Thermal resistance junction to ambient			R_{thJA}		60		K/W

LT2A01G–LT2A07G

Vishay Lite-On Power Semiconductor



Characteristics ($T_j = 25^\circ\text{C}$ unless otherwise specified)

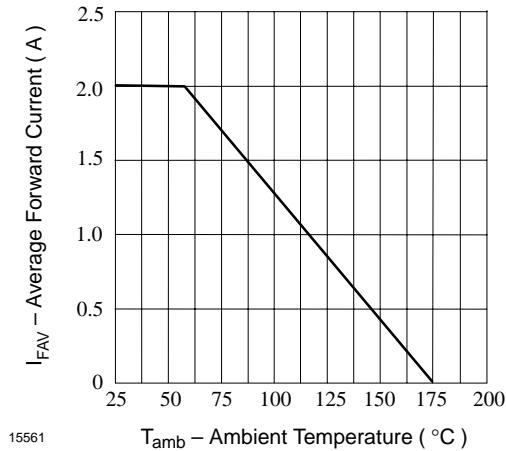


Figure 1. Max. Average Forward Current vs. Ambient Temperature

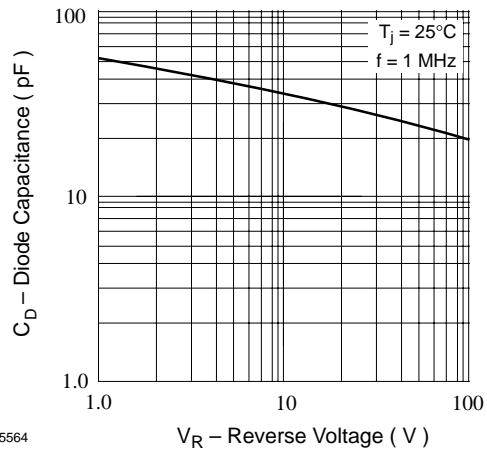


Figure 4. Typ. Diode Capacitance vs. Reverse Voltage

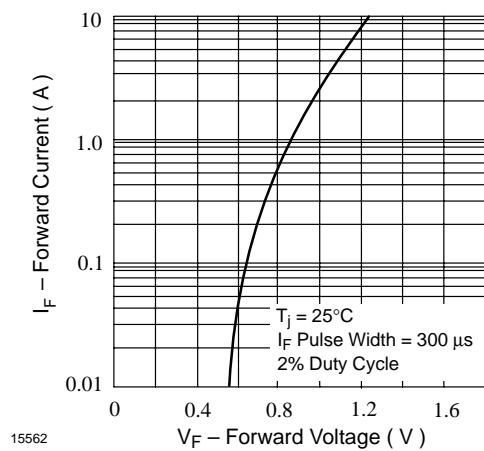


Figure 2. Typ. Forward Current vs. Forward Voltage

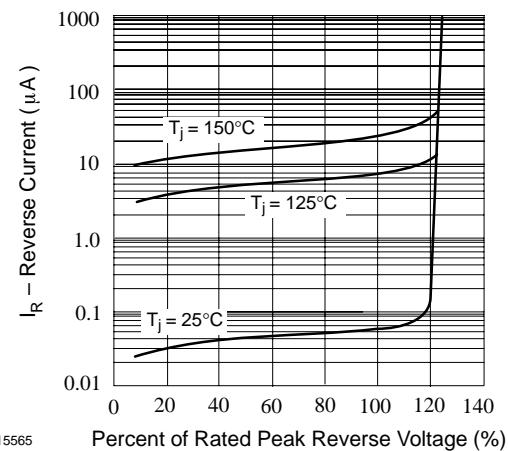


Figure 5. Typ. Reverse Current vs. Percent of Rated Peak Reverse Voltage

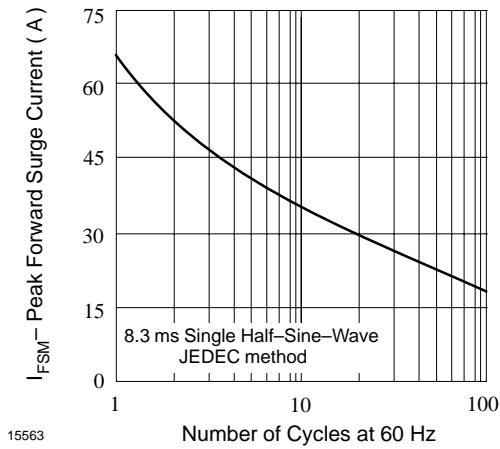


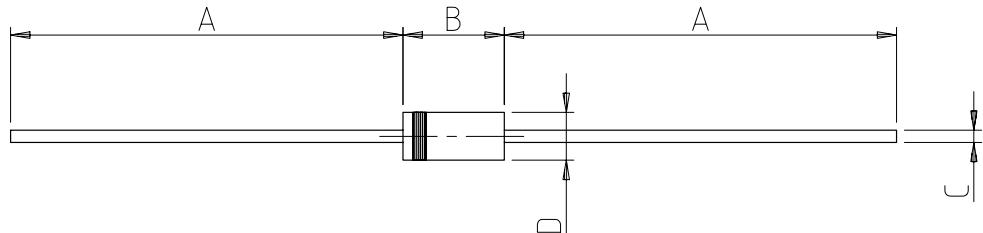
Figure 3. Max. Peak Forward Surge Current vs. Number of Cycles



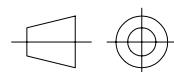
LT2A01G-LT2A07G

Vishay Lite-On Power Semiconductor

Dimensions in mm



D0-15		
Dim	Min	Max
A	25.40	-
B	5.50	7.62
C	0.686	0.889
D	2.60	3.6
All Dimensions in mm		



technical drawings
according to DIN
specifications

14442

Case: molded plastic

Polarity: cathode band

Approx. weight: 0.4 grams

Mounting position: any

Marking: type number



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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